

isc Silicon NPN Power Transistor

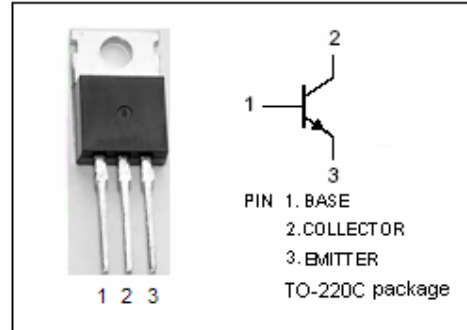
BD799

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 80V(\text{Min})$
- Low Saturation Voltage
- Complement to Type BD800

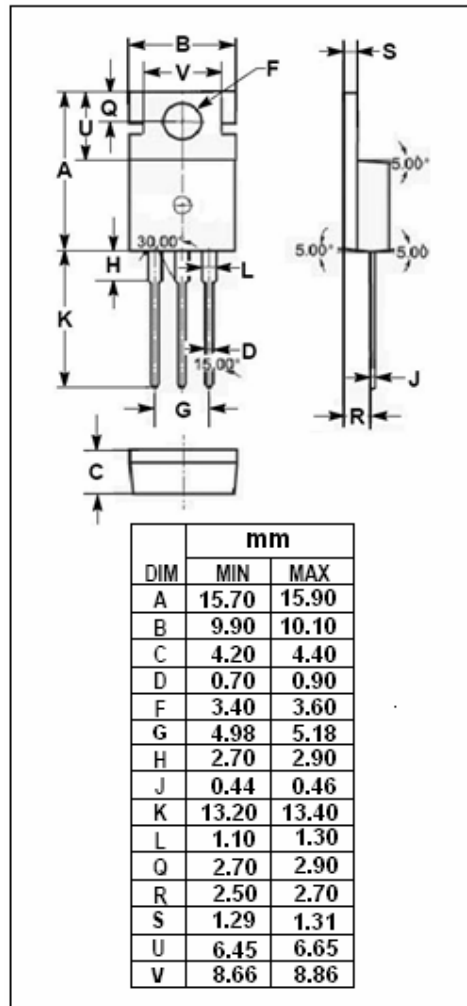
APPLICATIONS

- Designed for a wide variety of medium-power switching and amplifier applications , such as series and shunt regulators and driver and output stages of high-fidelity amplifiers.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	8	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation $T_c=25^{\circ}C$	65	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Ttemperature Range	-55~150	$^{\circ}C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.92	$^{\circ}C/W$

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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$			1	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}; V_{CE}=2\text{V}$			1.6	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1	mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=2\text{V}$	30			
h_{FE-2}	DC Current Gain	$I_C=3\text{A}; V_{CE}=2\text{V}$	15			
f_T	Current-Gain—Bandwidth Product	$I_C=0.25\text{A}; V_{CE}=10\text{V}, f_{test}=1\text{MHz}$	3			MHz